



DMT69M8LPS

60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Ι _D T _C = +25°C
60V	12mΩ @ V _{GS} = 10V	70A
007	14mΩ @ V _{GS} = 4.5V	55A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

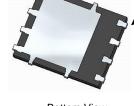
- High Frequency Switching
- Sync. Rectification
- DC-DC Converters

PowerDI5060-8



Top View

Notes:



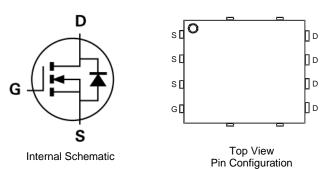
Bottom View

Features

- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMT69M8LPS-13	PowerDI5060-8	2,500/Tape & Reel

Pin1

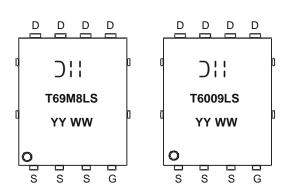
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



] ; ; = Manufacturer's Marking T69M8LS & T6009LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 - 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±16	V
Continuous Drain Current (Note 5)	T _A = +25°C T _A = +70°C	I _D	10.2 8.2	А
Continuous Drain Current (Note 6)	T _C = +25°C T _C = +70°C	I _D	70 55	А
Maximum Continuous Body Diode Forward Current (Note 6)	IS	100	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	160	А
Avalanche Current, L=0.1mH		I _{AS}	20.3	A
Avalanche Energy, L=0.1mH		E _{AS}	20.6	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{0JA}	53	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	PD	113	W
Thermal Resistance, Junction to Case (Note 6)	•	Rejc	1.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

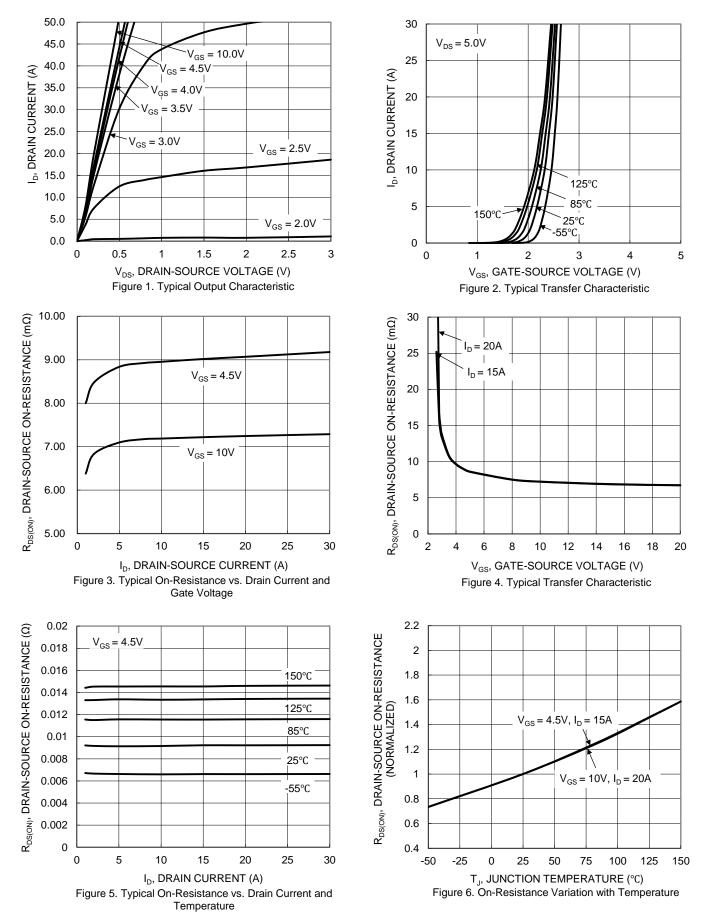
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	—	—	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.7	_	2	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D	—	9.8	12	mΩ	$V_{GS} = 10V, I_D = 13.5A$	
	R _{DS(ON)}	—	12	14	11152	$V_{GS} = 4.5V, I_D = 11.5A$	
Diode Forward Voltage	V _{SD}	—	0.9		V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	CISS	—	1,925	—		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	—	438	—	pF		
Reverse Transfer Capacitance	C _{RSS}	—	41	—			
Gate Resistance	R _G	—	1.7	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_{G}	-	33.5	_		V _{DS} = 30V, I _D = 13.5A	
Total Gate Charge (V _{GS} = 4.5V)	Q_G	_	15.6	_	nC		
Gate-Source Charge	Q _{GS}	-	4.7	_	nc		
Gate-Drain Charge	Q _{GD}	-	5.3	_			
Turn-On Delay Time	t _{D(ON)}		4.5	_		V _{DD} = 30V, V _{GS} = 10V,	
Turn-On Rise Time	t _R	_	8.6	_			
Turn-Off Delay Time	t _{D(OFF)}	—	35.9	—	ns	$R_{G} = 6\Omega, I_{D} = 13.5A$	
Turn-Off Fall Time	t _F	—	15.7	—			
Body Diode Reverse Recovery Time	t _{RR}	—	18.2	—	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	—	33.1	—	nC	I _F = 13.5A, di/dt = 400A/µs	

Notes:

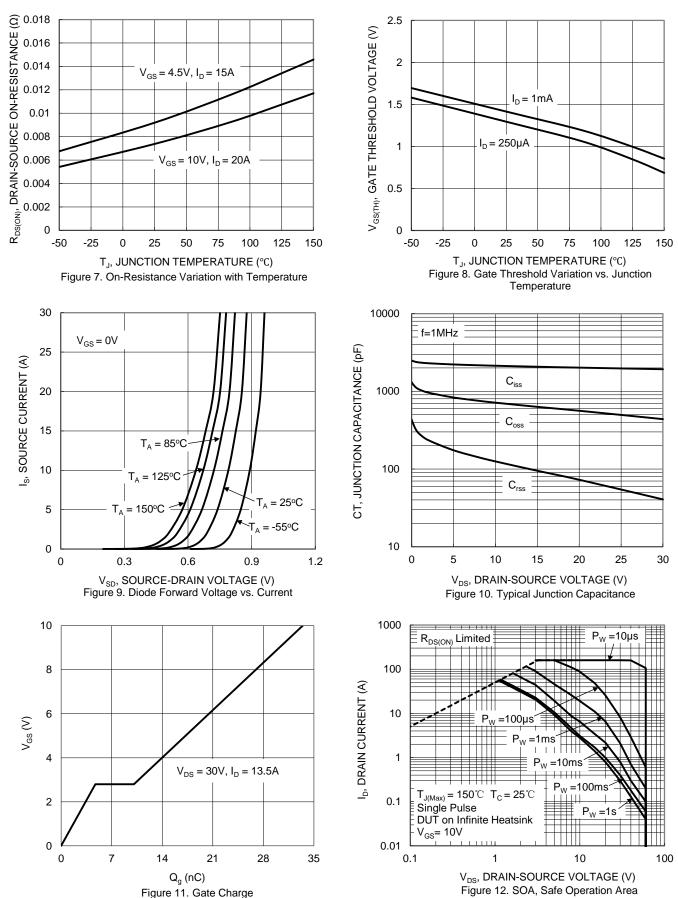
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





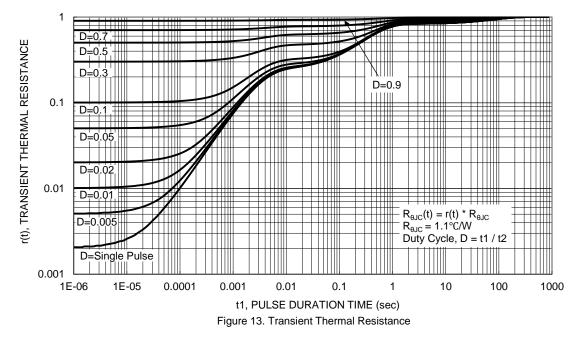
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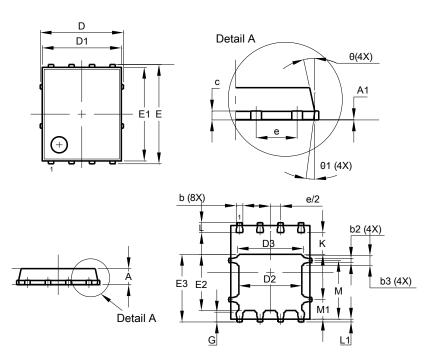






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



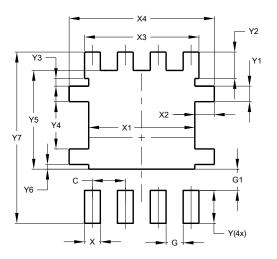
PowerDI5060-8

PowerDI5060-8						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	-			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D	Į	5.15 BSC	;			
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
Е	6.15 BSC					
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51	-	1			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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